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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I ² C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401cbu3

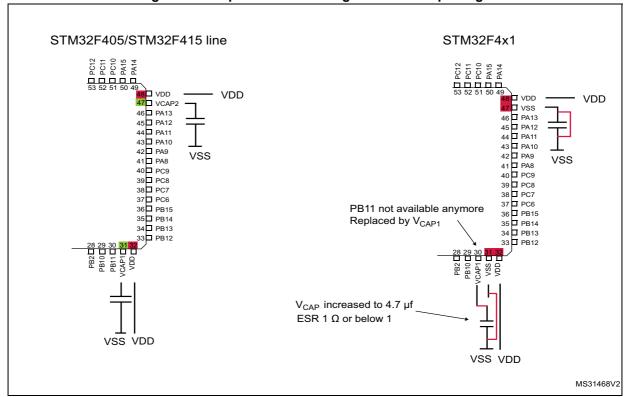


Figure 2. Compatible board design for LQFP64 package



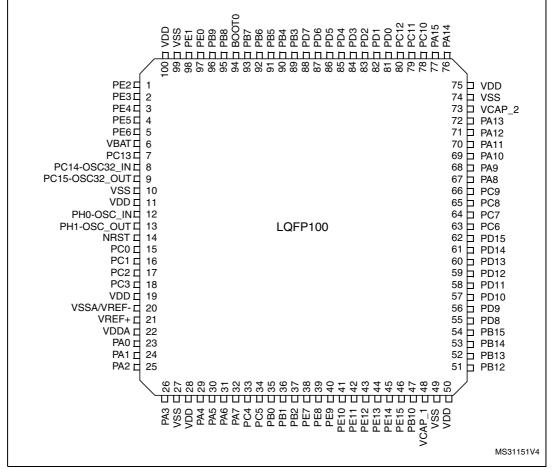


Figure 13. STM32F401xB/STM32F401xC LQFP100 pinout

1. The above figure shows the package top view.



Table 8. STM32F401xB/STM32F401xC pin definitions (continued)

	Pin	Nur	nber				ē			
UQFN48	WLCSP49	LQFP64	LQFP100	UFBGA100	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
13	E4	17	26	L3	PA3	I/O	FT	-	USART2_RX, TIM2_CH4, TIM5_CH4, TIM9_CH2, EVENTOUT	ADC1_IN3
-	-	18	27	-	VSS	S	-	-	-	-
-	-	19	28	-	VDD	S	-	-	-	-
-	-	-	-	E3	BYPASS_ REG	I	FT	-	-	-
14	G6	20	29	M3	PA4	I/O	FT	-	SPI1_NSS, SPI3_NSS/I2S3_WS, USART2_CK, EVENTOUT	ADC1_IN4
15	F5	21	30	K4	PA5	I/O	FT	-	SPI1_SCK, TIM2_CH1/TIM2_ETR, EVENTOUT	ADC1_IN5
16	F4	22	31	L4	PA6	I/O	FT	-	SPI1_MISO, TIM1_BKIN, TIM3_CH1, EVENTOUT	ADC1_IN6
17	F3	23	32	M4	PA7	I/O	FT	-	SPI1_MOSI, TIM1_CH1N, TIM3_CH2, EVENTOUT	ADC1_IN7
-	-	24	33	K5	PC4	I/O	FT	-	EVENTOUT	ADC1_IN14
-	-	25	34	L5	PC5	I/O	FT	-	EVENTOUT	ADC1_IN15
18	G5	26	35	M5	PB0	I/O	FT	-	TIM1_CH2N, TIM3_CH3, EVENTOUT	ADC1_IN8
19	G4	27	36	M6	PB1	I/O	FT	-	TIM1_CH3N, TIM3_CH4, EVENTOUT	ADC1_IN9
20	G3	28	37	L6	PB2	I/O	FT	-	EVENTOUT	BOOT1
-	-	-	38	M7	PE7	I/O	FT	-	TIM1_ETR, EVENTOUT	-
-	-	-	39	L7	PE8	I/O	FT	-	TIM1_CH1N, EVENTOUT	-
-	_	_	40	M8	PE9	I/O	FT	-	TIM1_CH1, EVENTOUT	-
-	-	-	41	L8	PE10	I/O	FT	-	TIM1_CH2N, EVENTOUT	-
_	-	-	42	M9	PE11	I/O	FT	-	SPI4_NSS, TIM1_CH2, EVENTOUT	-
-	-	-	43	L9	PE12	I/O	FT	-	SPI4_SCK, TIM1_CH3N, EVENTOUT	-
-	-	-	44	M10	PE13	I/O	FT	-	SPI4_MISO, TIM1_CH3, EVENTOUT	-

Table 8. STM32F401xB/STM32F401xC pin definitions (continued)

	Pin	Nun	nber				e.			,
UQFN48	WLCSP49	LQFP64	LQFP100	UFBGA100	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	39	65	E10	PC8	I/O	FT	-	USART6_CK, TIM3_CH3, SDIO_D0, EVENTOUT	-
-	-	40	66	D12	PC9	I/O	FT	-	I2S_CKIN, I2C3_SDA, TIM3_CH4, SDIO_D1, MCO_2, EVENTOUT	-
29	D1	41	67	D11	PA8	I/O	FT	-	I2C3_SCL, USART1_CK, TIM1_CH1, OTG_FS_SOF, MCO_1, EVENTOUT	-
30	D2	42	68	D10	PA9	I/O	FT	-	I2C3_SMBA, USART1_TX, TIM1_CH2, EVENTOUT	OTG_FS_VBUS
31	C2	43	69	C12	PA10	I/O	FT	-	USART1_RX, TIM1_CH3, OTG_FS_ID, EVENTOUT	-
32	C1	44	70	B12	PA11	I/O	FT	-	USART1_CTS, USART6_TX, TIM1_CH4, OTG_FS_DM, EVENTOUT	-
33	СЗ	45	71	A12	PA12	I/O	FT	-	USART1_RTS, USART6_RX, TIM1_ETR, OTG_FS_DP, EVENTOUT	-
34	В3	46	72	A11	PA13 (JTMS- SWDIO)	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
-	1	1	73	C11	VCAP_2	S	1	-	-	-
35	В1	47	74	F11	VSS	S	-	-	-	-
36	-	48	75	G11	VDD	S	-	-	-	-
-	B2	-	-	-	VDD	S	-	-	-	-
37	A1	49	76	A10	PA14 (JTCK- SWCLK)	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
38	A2	50	77	A9	PA15 (JTDI)	I/O	FT	-	JTDI, SPI1_NSS, SPI3_NSS/I2S3_WS, TIM2_CH1/TIM2_ETR, JTDI, EVENTOUT	-
-	ı	51	78	B11	PC10	I/O	FT	-	SPI3_SCK/I2S3_CK, SDIO_D2, EVENTOUT	-
-	ı	52	79	C10	PC11	I/O	FT	-	I2S3ext_SD, SPI3_MISO, SDIO_D3, EVENTOUT	-
-	1	53	80	B10	PC12	I/O	FT	-	SPI3_MOSI/I2S3_SD, SDIO_CK, EVENTOUT	-
-	-	-	81	С9	PD0	I/O	FT	1	EVENTOUT	-

				_		Tabl	e 9. Alter	nate funct	ion mapp	oing							
		AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
	Port	SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/SPI2/ I2S2/SPI3/ I2S3/SPI4	SPI2/I2S2/ SPI3/ I2S3	SPI3/I2S3/ USART1/ USART2	USART6	12C2/ 12C3	OTG1_FS		SDIO			
	PA0	-	TIM2_CH1/ TIM2_ETR	TIM5_CH1	-	-	-	-	USART2_ CTS	-	-	-	-	-	-	-	EVENT OUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_ RTS	-	-	-	-	-	-	-	EVENT OUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_ TX	-	-	-	-	-	-	-	EVENT OUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-		-	USART2_ RX	-	-	-	-	-	-	-	EVENT OUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS/ I2S3_WS	USART2_ CK	-	-	-	-	_	-	-	EVENT OUT
	PA5	-	TIM2_CH1/ TIM2_ETR	-	-	-	SPI1_SCK	-	-	-	-	-	-	_	-	-	EVENT OUT
	PA6	-	TIM1_BKIN	TIM3_CH1	-	-	SPI1_ MISO	-	-	-	-	-	-	-	-	-	EVENT OUT
4	PA7	-	TIM1_CH1N	TIM3_CH2	-	-	SPI1_ MOSI	-	-	-	-	-	-	-	-	-	EVENT OUT
Port	PA8	MCO_1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_ CK	-	-	OTG_FS_ SOF	-	-	-	-	EVENT OUT
	PA9	-	TIM1_CH2	-	-	I2C3_ SMBA	-	-	USART1_ TX	-	-	OTG_FS_ VBUS	-	-	-	-	EVENT OUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_ RX	-	-	OTG_FS_I D	-	-	-	-	EVENT OUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_ CTS	USART6_ TX	-	OTG_FS_ DM	-	-	-	-	EVENT OUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_ RTS	USART6_ RX	-	OTG_FS_ DP	-	-	-	1	EVENT OUT
	PA13	JTMS_ SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PA14	JTCK_ SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PA15	JTDI	TIM2_CH1/ TIM2_ETR	-	-	-	SPI1_NSS	SPI3_NSS/ I2S3_WS	-	-	-	-	-	-	-	-	EVENT OUT

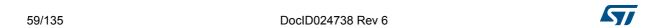


6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
ť	Internal ALID clock frequency	Power Scale3: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x01	0	-	60		
f _{HCLK}	Internal AHB clock frequency	Power Scale2: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x10	0	-	84	MHz	
f _{PCLK1}	Internal APB1 clock frequency		0	-	42		
f _{PCLK2}	Internal APB2 clock frequency		0	-	84		
V_{DD}	Standard operating voltage		1.7 ⁽¹⁾	-	3.6		
V _{DDA} (2)(3)	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as $V_{DD}^{(4)}$	1.7 ⁽¹⁾	-	2.4		
(2)(3)	Analog operating voltage (ADC limited to 2.4 M samples)	Must be the same potential as V _{DD}	2.4	-	3.6		
V _{BAT}	Backup operating voltage		1.65	-	3.6		
	Regulator ON: 1.2 V internal	VOS[1:0] bits in PWR_CR register = 0x01 Max frequency 60 MHz	1.08 ⁽⁵⁾	1.14	1.20 ⁽⁵⁾	V	
V ₁₂	voltage on V _{CAP_1} /V _{CAP_2} pins	VOS[1:0] bits in PWR_CR register = 0x10 Max frequency 84 MHz	1.20 ⁽⁵⁾	1.26	1.32 ⁽⁵⁾		
	Regulator OFF: 1.2 V external	Max. frequency 60 MHz.	1.1	1.14	1.2		
V ₁₂	voltage must be supplied on V_{CAP_1}/V_{CAP_2} pins	Max. frequency 84 MHz.	1.2	1.26	1.32		
	Input voltage on RST and FT	$2 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	-0.3	-	5.5		
V_{IN}	pins ⁽⁶⁾	$V_{DD} \le 2 V$	-0.3	-	5.2		
	Input voltage on BOOT0 pin		0	-	9		
		UFQFPN48	ı	-	625		
	Maximum allowed package	WLCSP49	ı	-	385	mW	
P_{D}	power dissipation for suffix 6	LQFP64	ı	-	313		
	and 7 ⁽⁷⁾	LQFP100	-	-	465		
		UFBGA100	-	-	323		



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{PDRhyst} ⁽²⁾	PDR hysteresis		-	40	-	mV
V	Brownout level 1	Falling edge	2.13	2.19	2.24	
V _{BOR1}	threshold	Rising edge	2.23	2.29	2.33	
V	Brownout level 2	Falling edge	2.44	2.50	2.56	V
V _{BOR2}	threshold	Rising edge	2.53	2.59	2.63	V
V	Brownout level 3	Falling edge	2.75	2.83	2.88	
V _{BOR3}	threshold	Rising edge	2.85	2.92	2.97	
V _{BORhyst} ⁽²⁾	BOR hysteresis		-	100	-	mV
T _{RSTTEMPO}	POR reset timing		0.5	1.5	3.0	ms
I _{RUSH} ⁽²⁾	InRush current on voltage regulator power- on (POR or wakeup from Standby)		1	160	200	mA
E _{RUSH} ⁽²⁾	InRush energy on voltage regulator power- on (POR or wakeup from Standby)	V _{DD} = 1.7 V, T _A = 105 °C, I _{RUSH} = 171 mA for 31 μs	-	-	5.4	μC

Table 19. Embedded reset and power control block characteristics (continued)

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 19: Current consumption measurement scheme*.

All the run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

^{1.} The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.

^{2.} Guaranteed by design.

^{3.} The reset timing is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is fetched by the user application code.

Table 21. Typical and maximum current consumption, code with data processing (ART
accelerator disabled) running from SRAM

Cymhal	Parameter	Conditions	f _{HCLK}	Turn			l lmi4	
Symbol	Parameter		(MHz)	Тур	T _A = 25 °C	T _A =85 °C	T _A =105 °C	Unit
			84	20.2	21	22	23	
	Supply current	External clock, all peripherals enabled ⁽²⁾⁽³⁾ External clock, all peripherals disabled ⁽³⁾	60	14.7	15	16	18	
			40	10.7	11	12	13	
			20	5.7	6	7	8	mA
I _{DD}	in Run mode		84	11.2	12	13	14	IIIA
			60	8.2	9	10	11	
			40	6.1	7	8	9	
			20	3.4	4	5	6	

- 1. Guaranteed by characterization, unless otherwise specified.
- 2. When analog peripheral blocks such as ADC, HSE, LSE, HSI, or LSI are ON, an additional power consumption has to be considered
- 3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.

Table 22. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory- V_{DD} = 1.8 V

						Max ⁽¹⁾		Unit
Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Тур	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
			84	22.2	23	24	25	
		60	14.5	15	16	17		
	Supply current	External clock, all peripherals enabled ⁽²⁾⁽³⁾	40	10.7	11	12	13	
			30	8.6	9	10	11	
			20	7.0	8	9	10	mA
I _{DD}	in Run mode		84	11.5	12	13	14	IIIA
			60	7.7	8	9	10	
		External clock, all peripherals disabled ⁽³⁾	40	5.6	6	7	8	
		an pompriorate disabled	30	4.5	5	6	7	
			20	3.8	5	6	7	

^{1.} Guaranteed by characterization, unless otherwise specified.



^{2.} Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).

^{3.} When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Table 32. Switching output I/O current consumption

Symbol	Parameter	Conditions ⁽¹⁾	I/O toggling frequency (f _{SW})	Тур	Unit
			2 MHz	0.05	
			8 MHz	0.15	
		V _{DD} = 3.3 V	25 MHz	0.45	
		$C = C_{INT}^{(2)}$	50 MHz	0.85	
			60 MHz	1.00	
			84 MHz	1.40	
			2 MHz	0.10	
			8 MHz	0.35	
		$V_{DD} = 3.3 V$ $C_{EXT} = 0 pF$	25 MHz	1.05	
		$C = C_{INT} + C_{EXT} + C_{S}$	50 MHz	2.20	
		INT EXT O	60 MHz	2.40	
IDDIO	I/O switching current		84 MHz	3.55	
			2 MHz	0.20	mA
		V_{DD} = 3.3 V C_{EXT} =10 pF C = C_{INT} + C_{EXT} + C_{S}	8 MHz	0.65	
			25 MHz	1.85	
			50 MHz	2.45	
		27.1	60 MHz	4.70	1
			84 MHz	8.80	
			2 MHz	0.25	
		V _{DD} = 3.3 V	8 MHz	1.00	
		C _{EXT} = 22 pF	25 MHz	3.45	
		$C = C_{INT} + C_{EXT} + C_{S}$	50 MHz	7.15	
			60 MHz	11.55	
			2 MHz	0.32	
		$V_{DD} = 3.3 \text{ V}$ $C_{EXT} = 33 \text{ pF}$	8 MHz	1.27]
		$C = C_{INT} + C_{EXT} + C_{S}$	25 MHz	3.88	
		27.1	50 MHz	12.34	

^{1.} C_S is the PCB board capacitance including the pad pin. C_S = 7 pF (estimated value).

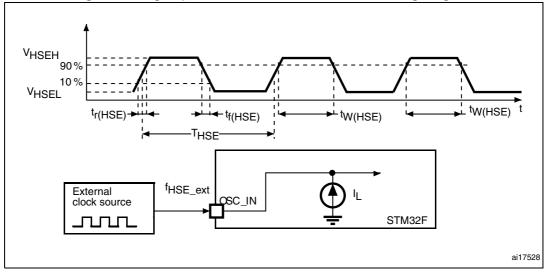
^{2.} This test is performed by cutting the LQFP100 package pin (pad removal).

Table 36. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSE_ext}	User External clock source frequency ⁽¹⁾		-	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V
V _{LSEL}	OSC32_IN input pin low level voltage		V _{SS}	-	0.3V _{DD}	
$\begin{matrix} t_{\text{w(LSE)}} \\ t_{\text{f(LSE)}} \end{matrix}$	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	113
C _{in(LSE)}	OSC32_IN input capacitance ⁽¹⁾		-	5	-	pF
DuCy _(LSE)	Duty cycle		30	-	70	%
IL	OSC32_IN Input leakage current	$V_{SS} \le V_{IN} \le V_{DD}$	-	-	±1	μA

^{1.} Guaranteed by design.

Figure 22. High-speed external clock source AC timing diagram



series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note:

For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

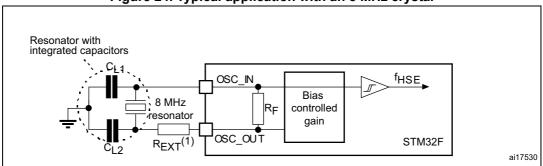


Figure 24. Typical application with an 8 MHz crystal

1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 38*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _F	Feedback resistor		-	18.4	-	МΩ
I _{DD}	LSE current consumption		-	-	1	μA
G _m _crit_max	Maximum critical crystal g _m	Startup	-	-	0.56	μA/V
t _{SU(LSE)} ⁽²⁾	startup time	V _{DD} is stabilized	-	2	-	s

Table 38. LSE oscillator characteristics (f_{LSE} = 32.768 kHz) ⁽¹⁾

Note:

For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



^{1.} Guaranteed by design.

t_{SU(LSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is guaranteed by characterization. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Table 41. Main PLL characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DD(PLL)} ⁽⁴⁾	PLL power consumption on VDD	VCO freq = 192 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
I _{DDA(PLL)} ⁽⁴⁾	PLL power consumption on VDDA	VCO freq = 192 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	IIIA

Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.

Table 42. PLLI2S (audio PLL) characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f _{PLLI2S_IN}	PLLI2S input clock ⁽¹⁾			0.95 ⁽²⁾	1	2.10	
f _{PLLI2S_OUT}	PLLI2S multiplier output clock			-	-	216	MHz
f _{VCO_OUT}	PLLI2S VCO output			192	ī	432	
+	PLLI2S lock time	VCO freq = 192 MHz	<u> </u>	75	-	200	μs
t _{LOCK}	PLLI25 lock time	VCO freq = 432 MHz	<u> </u>	100	-	300	
		Cycle to cycle at	RMS	-	90	-	
Jitter ⁽³⁾	Master I2S clock jitter	12.288 MHz on 48 KHz period, N=432, R=5	peak to peak	-	±280	-	
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples		-	90	-	ps
	WS I2S clock jitter Cycle to cycle at 48 KHz on 1000 samples		-	400	-		
I _{DD(PLLI2S)} ⁽⁴⁾	PLLI2S power consumption on V _{DD}	VCO freq = 192 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mΛ
I _{DDA(PLLI2S)} ⁽⁴⁾	PLLI2S power consumption on V _{DDA}	VCO freq = 192 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	- mA

^{1.} Take care of using the appropriate division factor M to have the specified PLL input clock values.

^{2.} Guaranteed by design.

^{3.} The use of 2 PLLs in parallel could degraded the Jitter up to +30%.

^{4.} Guaranteed by characterization.

^{2.} Guaranteed by design.

^{3.} Value given with main PLL running.

^{4.} Guaranteed by characterization.

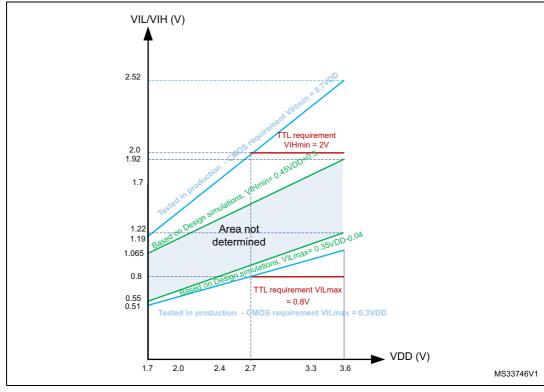


Figure 30. FT I/O input characteristics

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14 and PC15 which can sink or source up to ± 3 mA. When using the PC13 to PC15 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*. In particular:

- The sum of the currents sourced by all the I/Os on V_{DD}, plus the maximum Run consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 12*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 12*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.



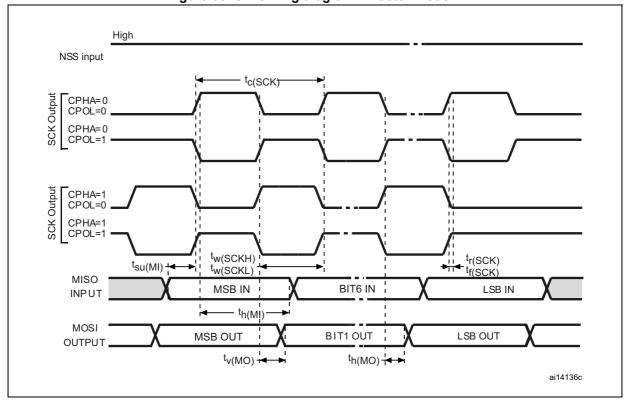


Figure 36. SPI timing diagram - master mode⁽¹⁾

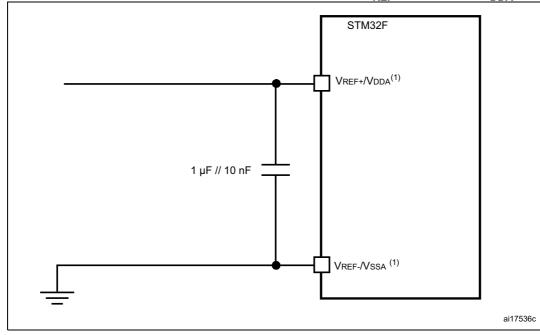


Figure 43. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})

V_{REF+} and V_{REF-} inputs are both available on UFBGA100. V_{REF+} is also available on LQFP100. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

6.3.21 Temperature sensor characteristics

Table 72. Temperature sensor characteristics

Symbol	Parameter	Min	Тур	Max	Unit
T _L ⁽¹⁾	V _{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope ⁽¹⁾	Average slope	-	2.5	-	mV/°C
V ₂₅ ⁽¹⁾	Voltage at 25 °C	-	0.76	-	V
t _{START} (2)	Startup time	-	6	10	μs
T _{S_temp} ⁽²⁾	ADC sampling time when reading the temperature (1 $^{\circ}\text{C}$ accuracy)	10	-	-	μs

^{1.} Guaranteed by characterization.

Table 73. Temperature sensor calibration values

Symbol	Parameter	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V _{DDA} = 3.3 V	0x1FFF 7A2C - 0x1FFF 7A2D
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C, V _{DDA} = 3.3 V	0x1FFF 7A2E - 0x1FFF 7A2F

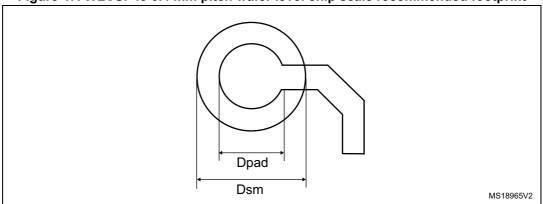
^{2.} Guaranteed by design.

Table 79. WLCSP49 - 49-ball, 2.965 x 2.965 mm, 0.4 mm pitch wafer level chip scale package mechanical data

	millimeters			inches ⁽¹⁾			
Symbol	Min	Тур	Max	Min	Тур	Max	
Α	0.525	0.555	0.585	0.0207	0.0219	0.0230	
A1	-	0.175	-	-	0.0069	-	
A2	-	0.380	-	-	0.0150	-	
A3 ⁽²⁾	-	0.025	-	-	0.0010	-	
b ⁽³⁾	0.220	0.250	0.280	0.0087	0.0098	0.0110	
D	2.930	2.965	3.000	0.1154	0.1167	0.1181	
E	2.930	2.965	3.000	0.1154	0.1167	0.1181	
е	-	0.400	-	-	0.0157	-	
e1	-	2.400	-	-	0.0945	-	
e2	-	2.400	-	-	0.0945	-	
F	-	0.2825	-	-	0.0111	-	
G	-	0.2825	-	-	0.0111	-	
aaa	-	0.100	-	-	0.0039	-	
bbb	-	0.100	-	-	0.0039	-	
ccc	-	0.100	-	-	0.0039	-	
ddd	-	0.050	-	-	0.0020	-	
eee	-	0.050	-	-	0.0020	-	

- 1. Values in inches are converted from mm and rounded to 4 decimal digits.
- 2. Back side coating.
- 3. Dimension is measured at the maximum bump diameter parallel to primary datum ${\sf Z}$.

Figure 47. WLCSP49 0.4 mm pitch wafer level chip scale recommended footprint





UFQFPN48 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

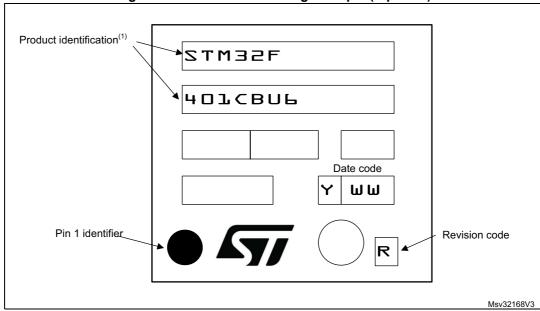


Figure 51. UFQFPN48 marking example (top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

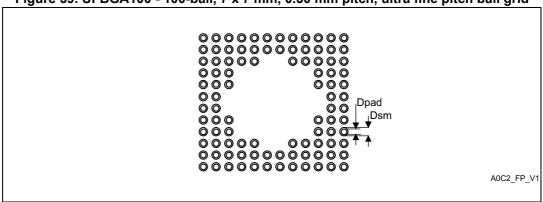


Table 84. UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol		millimeters			inches ⁽¹⁾		
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	
ddd	-	-	0.100	-	-	0.0039	
eee	-	-	0.150	-	-	0.0059	
fff	-	-	0.050	-	-	0.0020	

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 59. UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid



array
package recommended footprint

Table 85. UFBGA100 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm



UFBGA100 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

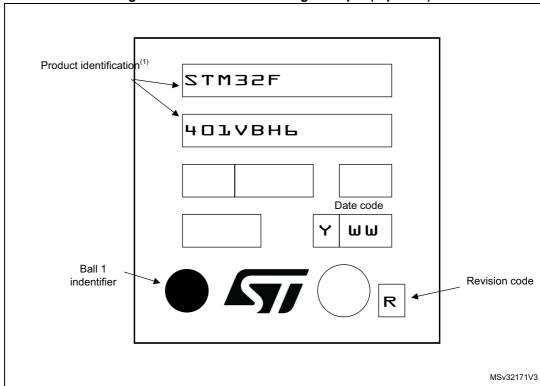


Figure 60. UFBGA100 marking example (top view)

^{1.} Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

9 Revision history

Table 88. Document revision history

Date	Revision	Changes
23-Jul-2013	1	Initial release.
06-Sep-2013	2	Updated product status to production data Added I2C 1 MBit/s in Features Updated Figure 1: Compatible board design for LQFP100 package Added notes and revised the main function after reset columnn Table 8: STM32F401xB/STM32F401xC pin definitions. Replaced 'I2S2_CKIN' signal name with 'I2S_CKIN' and added EVENTOUT alternate function in Table 8: STM32F401xB/STM32F401xC pin definitions and Table 9: Alternate function mapping Updated Section 3.28: Analog-to-digital converter (ADC) Updated the reference of V _{ESD(CDM)} in Table 51: ESD absolute maximum ratings Updated Section 3.20: Inter-integrated circuit interface (I2C), including Table 5: Comparison of I2C analog and digital filters Removed first sentence ("Unless otherwise specified") in I2C interface characteristics Changed the order of the tables in Section 6.3.6: Supply current characteristics Modified the "SDA and SCL rise time" fast mode I2C minimum value in Table 59: I ² C characteristics Updated Figure 33: I ² C bus AC waveforms and measurement circuit and Table 60: SCL frequency (f _{PCLK1} = 42 MHz, V _{DD} = V _{DD_I2C} = 3.3 V) Replaced "Marking of engineering samples" sections with "Marking of samples" sections, and added UFBGA100 device marking section for package UFGBA100 in Section 7: Package information
08-Nov-2013	3	Updated UFBGA100 in <i>Table 86: Package thermal characteristics</i> . Changed WLCSP49 package measurements to 3 x 3 mm in <i>Section 7.1</i> .